

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
-60V	60mΩ @ V _{GS} = -10V	-18.8A
	80mΩ @ V _{GS} = -4.5V	-16.8A

Features and Benefits

- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low R_{DS(ON)} — Ensures Minimal On-State Losses
- Wettable Flank for Improved Optical Inspection
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](mailto:contact@diodes.com) or your local Diodes representative.
<https://www.diodes.com/quality/product-definitions/>

Description and Applications

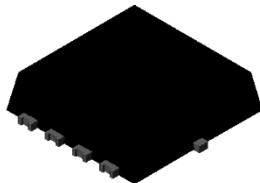
This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- Motor controls
- Power-management functions
- DC-DC converters

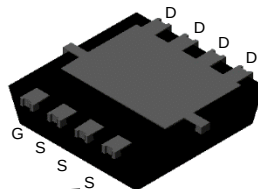
Mechanical Data

- Package: PowerDI[®]3333-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 
- Weight: 0.072 grams (Approximate)

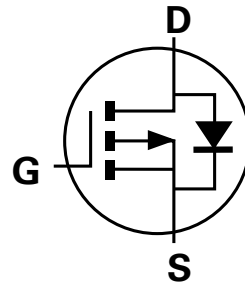
PowerDI3333-8/SWP (Type UX)



Top View



Pin 1 Bottom View



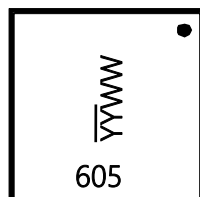
Equivalent Circuit

Ordering Information (Note 4)

Orderable Part Number	Package	Packing	
		Qty.	Carrier
DMP6051SFVW-7	PowerDI3333-8/SWP (Type UX)	2000	Tape & Reel
DMP6051SFVW-13	PowerDI3333-8/SWP (Type UX)	3000	Tape & Reel

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 - See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



605 = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 24 = 2024)
WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	-60	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = -10V	I _D	T _C = +25°C -18.8 T _C = +70°C -15.1	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)	I _{DM}	-75	A
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	-20.6	A
Pulsed Source Current (10μs Pulse, Duty Cycle = 1%)	I _{SM}	-75	A
Avalanche Current, L = 0.1mH	I _{AS}	-27	A
Avalanche Energy, L = 0.1mH	E _{AS}	36	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	2.7	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	47	°C/W
Total Power Dissipation (Note 6)	P _D	43	W
Thermal Resistance, Junction to Case (Note 6)	R _{θJC}	2.9	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-60	—	—	V	V _{GS} = 0, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	μA	V _{DS} = -60V, V _{GS} = 0
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	-1	—	-3	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	48	60	mΩ	V _{GS} = -10V, I _D = -7A
		—	62	80		V _{GS} = -4.5V, I _D = -7A
Diode Forward Voltage	V _{SD}	—	-0.8	-1.2	V	V _{GS} = 0, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	2087	—	pF	V _{DS} = -30V, V _{GS} = 0, f = 1MHz
Output Capacitance	C _{oss}	—	94	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	78	—	pF	
Gate Resistance	R _g	—	3.5	—	Ω	V _{DS} = 0, V _{GS} = 0, f = 1MHz
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	17	—	nC	V _{DS} = -30V, I _D = -5A
Total Gate Charge (V _{GS} = -10V)	Q _g	—	36	—	nC	
Gate-Source Charge	Q _{gs}	—	3.7	—	nC	
Gate-Drain Charge	Q _{gd}	—	5.6	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	6.5	—	ns	V _{DD} = -30V, V _{GS} = -10V, R _G = 3Ω, I _D = -5A
Turn-On Rise Time	t _R	—	19	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	40	—	ns	
Turn-Off Fall Time	t _F	—	24	—	ns	
Body Diode Reverse-Recovery Time	t _{RR}	—	23	—	ns	I _F = -5A, di/dt = 100A/μs
Body Diode Reverse-Recovery Charge	Q _{RR}	—	21	—	nC	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
6. Thermal resistance from junction to soldering point (on the exposed drain pad).
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

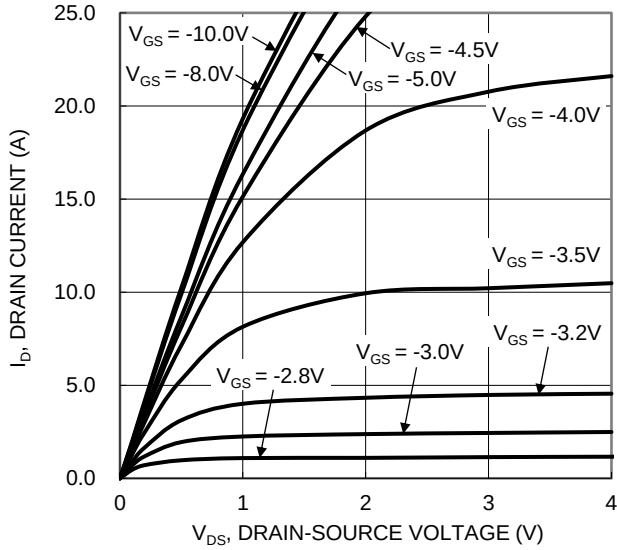


Figure 1. Typical Output Characteristic

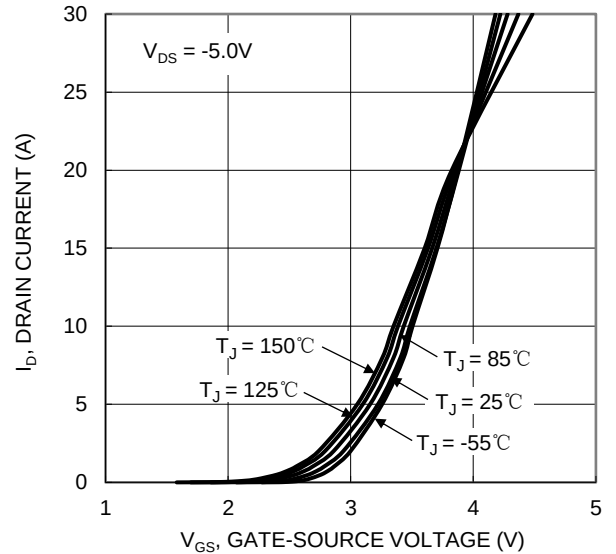


Figure 2. Typical Transfer Characteristic

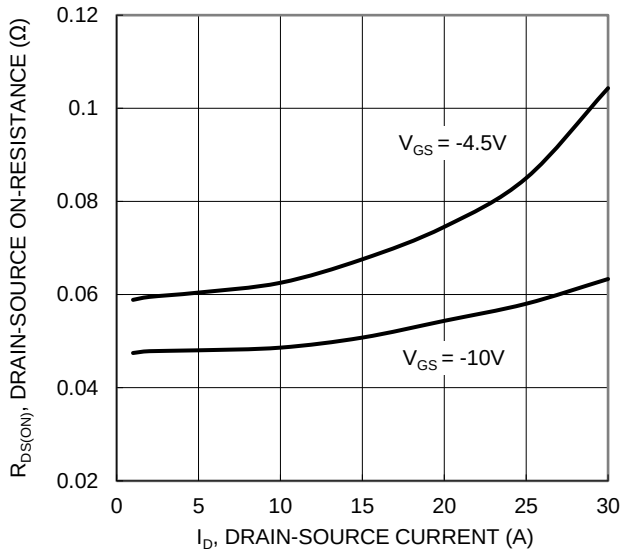


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

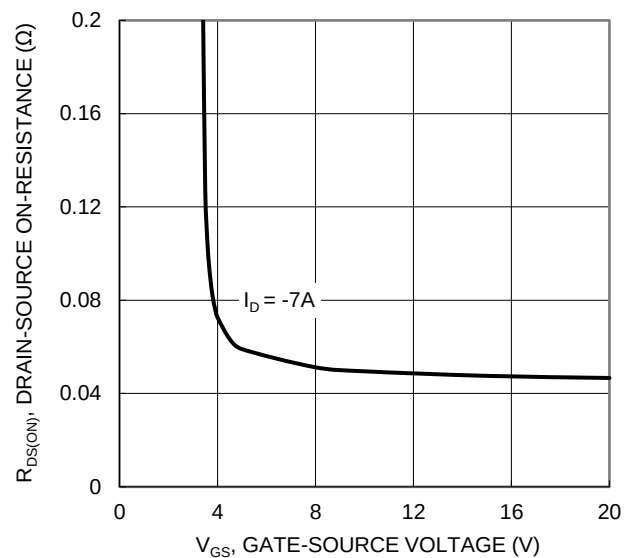


Figure 4. Typical Transfer Characteristic

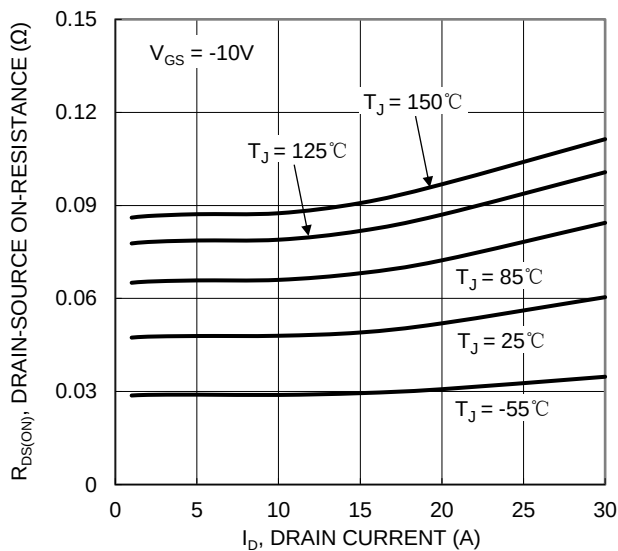


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

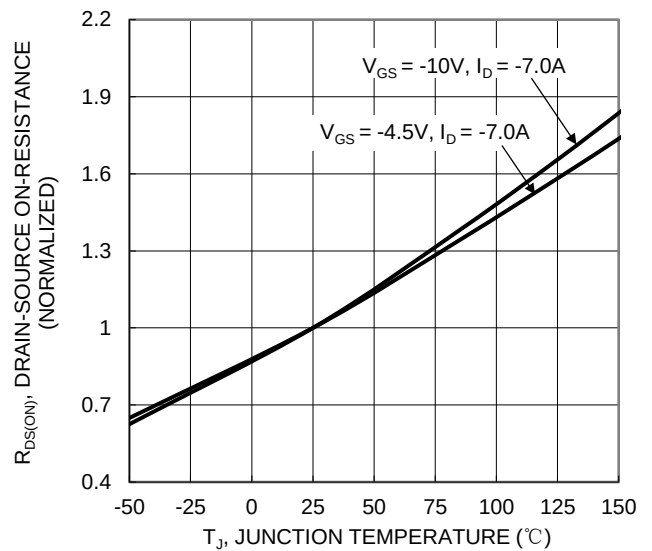


Figure 6. On-Resistance Variation with Junction Temperature

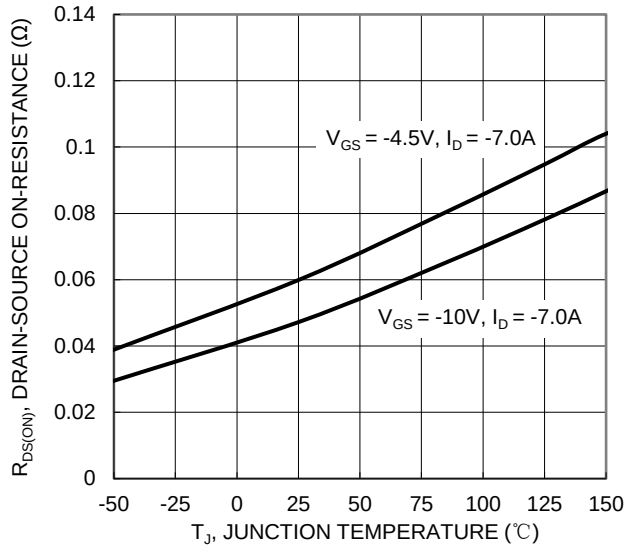


Figure 7. On-Resistance Variation with Junction Temperature

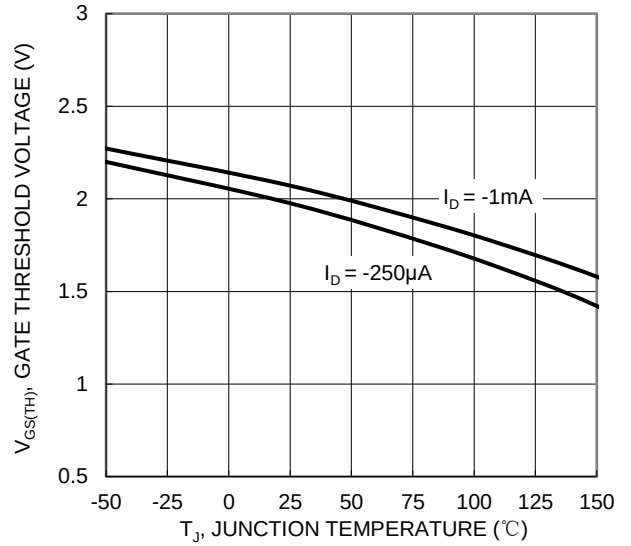


Figure 8. Gate Threshold Variation vs. Junction Temperature

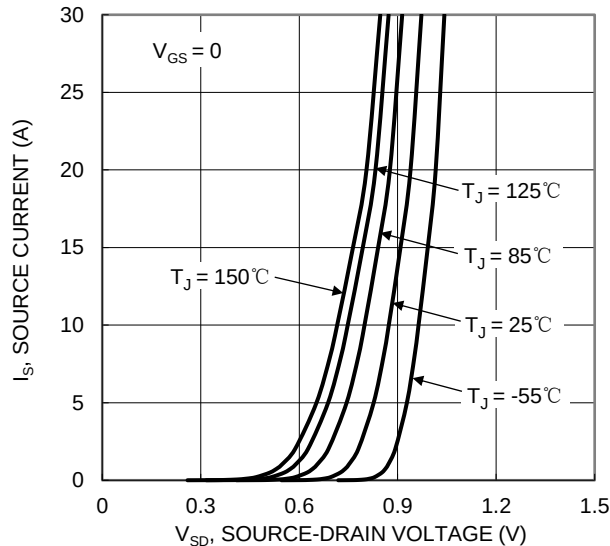


Figure 9. Diode Forward Voltage vs. Current

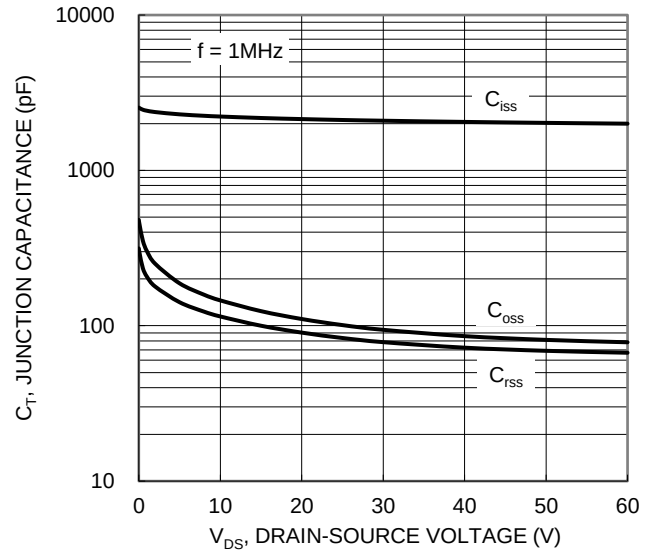


Figure 10. Typical Junction Capacitance

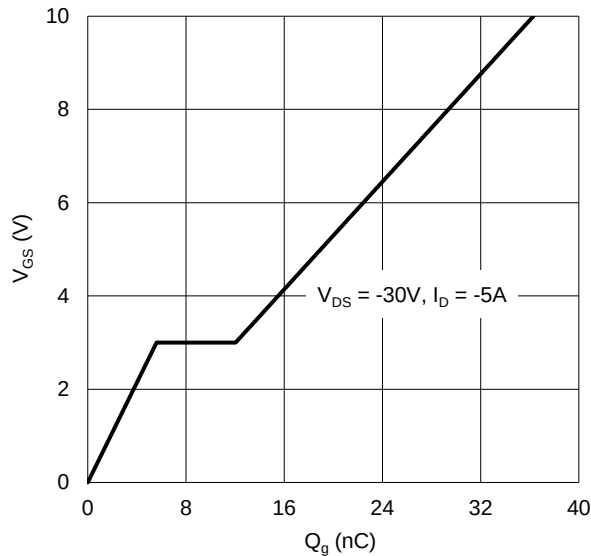


Figure 11. Gate Charge

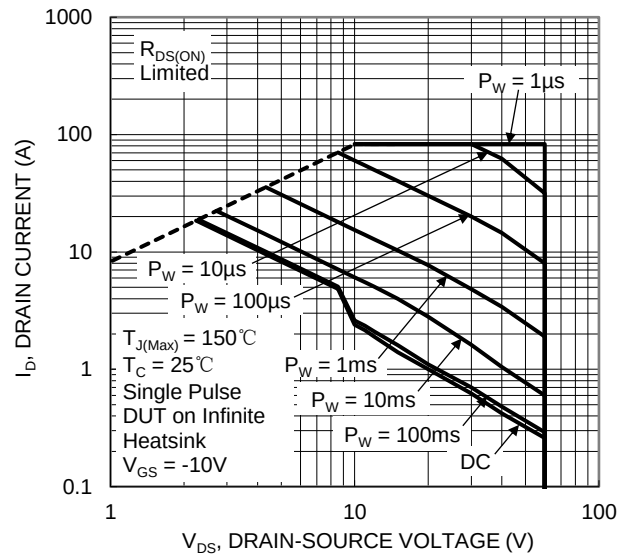


Figure 12. SOA, Safe Operation Area

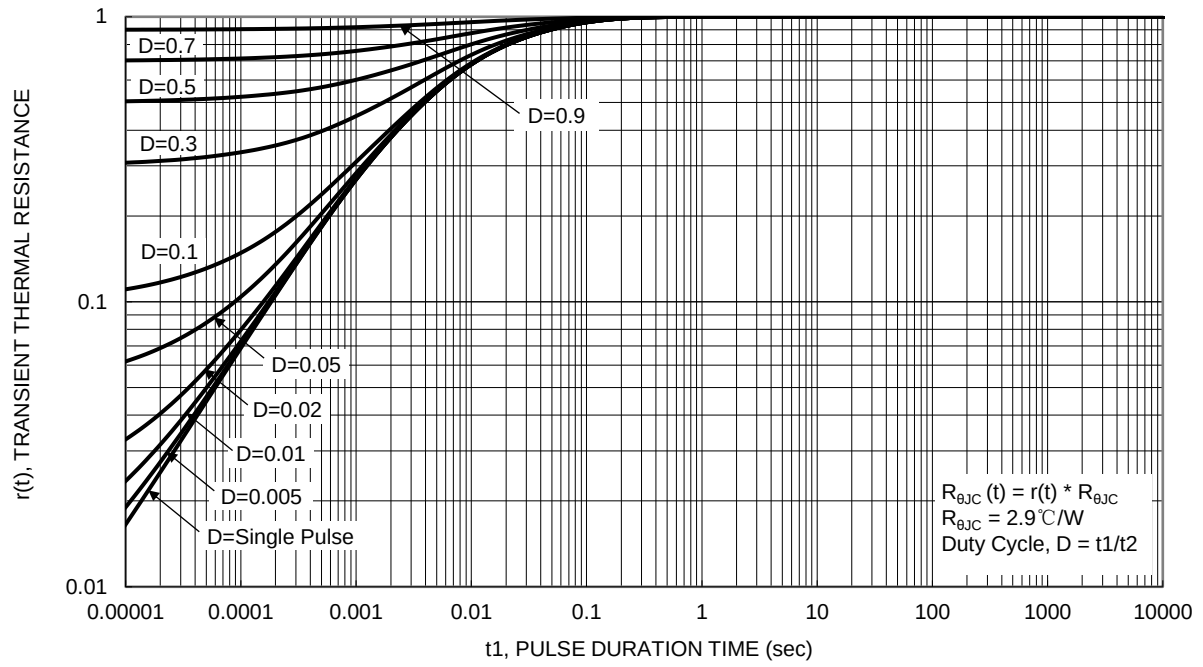
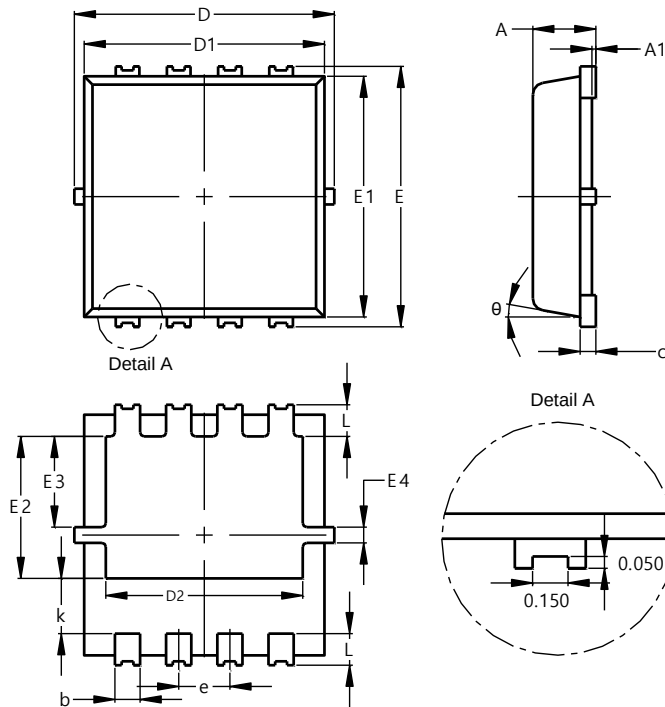


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI3333-8/SWP (Type UX)

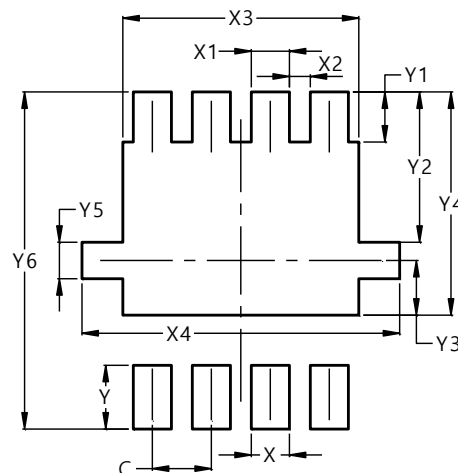


PowerDI3333-8/SWP (Type UX)			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	--
b	0.25	0.40	0.32
c	0.10	0.25	0.15
D	3.20	3.40	3.30
D1	2.95	3.15	3.05
D2	2.30	2.70	2.50
E	3.20	3.40	3.30
E1	2.95	3.15	3.05
E2	1.60	2.00	1.80
E3	0.95	1.35	1.15
E4	0.10	0.30	0.20
e	--	--	0.65
k	0.50	0.90	0.70
L	0.30	0.50	0.40
θ	0°	12°	10°
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI3333-8/SWP (Type UX)



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.600
X4	3.500
Y	0.700
Y1	0.550
Y2	1.650
Y3	0.600
Y4	2.450
Y5	0.400
Y6	3.700

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